

IN THE SPECIFICATION:

Please amend the paragraph following the section title "CROSS-REFERENCE TO RELATED APPLICATION" on page 2 of the application and immediately preceding paragraph [0001] as follows:

This application is a divisional of application Serial No. 09/615,009, filed July 12, 2000, ~~pending~~, now U.S. Patent 6,525,413, issued February 25, 2003.

Please amend paragraph number [0007] as follows:

[0007] Other types of multi-chip modules that include one or more semiconductor dice that are flip-chip bonded to a carrier are also known. None of these multi-chip modules, however, ~~includes~~ include semiconductor dice that are directly flip-chip bonded to one another with the subsequent assembly then being flip-chip mounted to a substrate.

Please amend paragraph number [0008] as follows:

[0008] Keeping in mind the trend toward faster computers and other electronic devices, the use of intermediate conductive elements, such as wire bonds, and the conductive traces of carrier substrates to electrically connect the semiconductor dice of a multi-chip module is somewhat undesirable since the electrical paths of these types of connections are typically lengthy and, consequently, limit the speed with which the semiconductor dice of the multi-chip module may communicate with one another. The affects that these types of connections in conventional multi-chip modules have on the speed at which an electronic device, such as a computer, operates are particularly undesirable when one of the semiconductor dice of the ~~multi-chip~~ multi-chip module is a microprocessor and the other semiconductor dice of the multi-chip module are semiconductor devices with which the microprocessor should quickly communicate.

Please amend paragraph number [0041] as follows:

[0041] As corresponding bond pads 14 and 24 are electrically connected to one another by way of conductive structures 28, the physical lengths of electrical circuits including

conductive structures 28 are much shorter than the physical lengths of circuits including wire bonds or conductive traces of carrier substrates, as have been employed in conventional ~~multi-chip~~ multi-chip modules. Accordingly, first semiconductor die 10 may communicate with connected semiconductor dice, such as second semiconductor die 20, at much faster rates than are possible with conventional multi-chip modules.

Please amend paragraph number [0058] as follows:

[0058] A variation of an assembly 130' incorporating teachings of the present invention, shown in FIG. 12, includes the same elements as assembly 130, shown in FIG. 11, except for conductive structures 117. Rather, assembly 130' includes conductive structures 117' that include two members 117a' and 117b'. ~~Members~~ Member 117a' may be predisposed on outer bond pads 114b of first semiconductor die 110, while ~~members~~ member 117b' may be predisposed on contact pads 164 of carrier substrate 160. The collective distances that members 117a' and 117b' protrude from active surface 112 and surface 162, respectively, are about equal to $L + T + D$. As first semiconductor die 110 is invertedly oriented and aligned over carrier substrate 160, members 117a' and 117b' of each conductive structure 117' are aligned and abut one another. Upon reflowing the conductive material of members 117a' and 117b' or otherwise securing corresponding members 117a' and 117b' to one another, integral conductive structures 117' that electrically connect corresponding outer bond pads 114b and contact pads 164 to each other are formed.